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Applications : AC100V~200V three-phase inverter drive for small power motor control.

Integrated Power Functions :

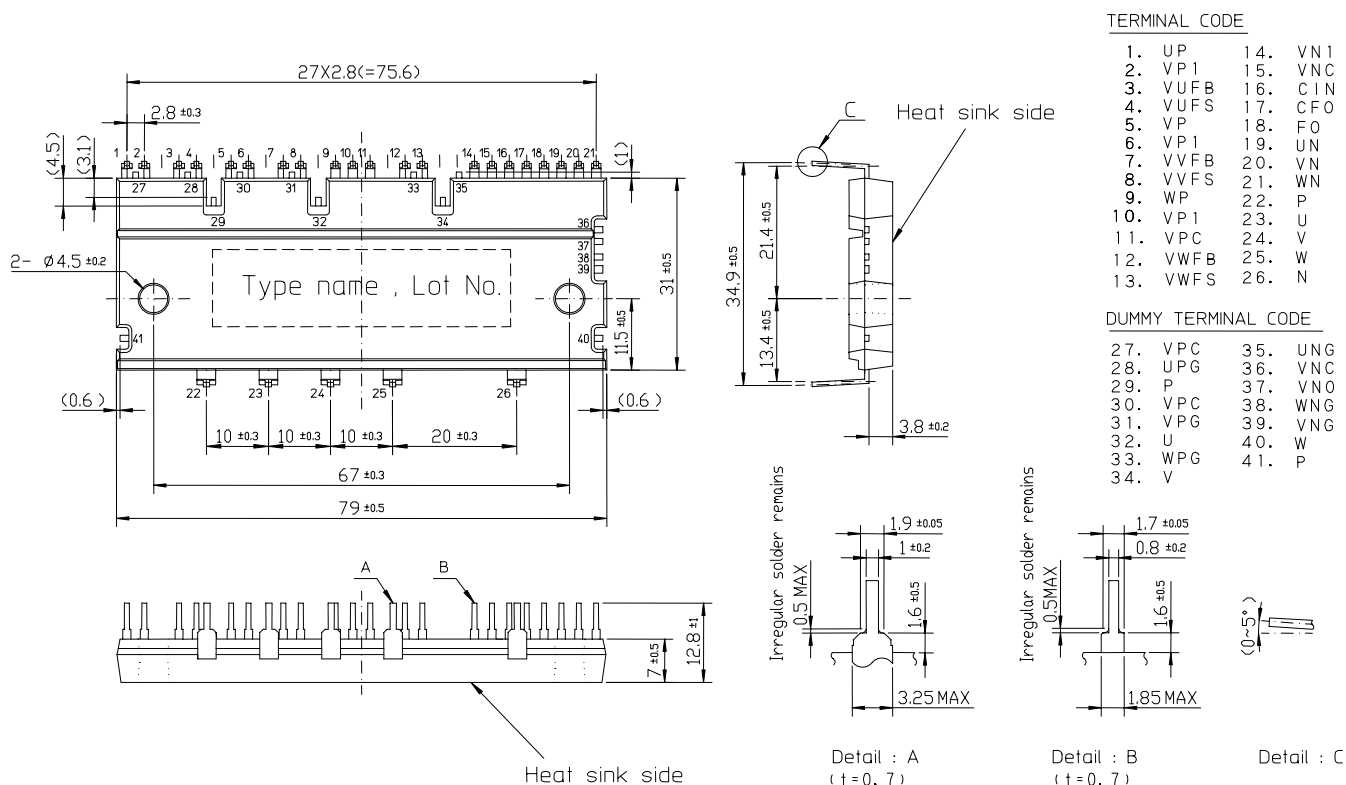
600V/30A low-loss 5th generation IGBT inverter bridge for 3 phase DC-to-AC power conversion

Integrated drive, protection and system control functions :

- For upper-leg IGBTs : Drive circuit, High voltage isolated high-speed level shifting, Control supply under-voltage (UV) protection.
- For lower-leg IGBTs : Drive circuit, Control supply under-voltage protection (UV), Short circuit protection (SC). (Fig.3)
- Fault signaling : Corresponding to an SC fault (Lower-side IGBT) or a UV fault (Low-sideer supply).
- Input interface : 5V line CMOS/TTL compatible.(high Active)

UL Approved : Yellow Card No. E80276

Fig. 1 Package Outlines



Maximum Ratings ($T_j=25\text{ }^\circ\text{C}$, unless otherwise noted) :

Inverter Part :

Item	Symbol	Condition	Rating	Unit
Supply voltage	V_{CC}	Applied between P-N	450	V
Supply voltage (surge)	$V_{CC(surge)}$	Applied between P-N	500	V
Collector-emitter voltage	V_{CES}		600	V
Each IGBT collector current	$\pm I_C$	$T_f=25\text{ }^\circ\text{C}$	30	A
Each IGBT collector current (peak)	$\pm I_{CP}$	$T_f=25\text{ }^\circ\text{C}$, less than 1ms	60	A
Collector dissipation	P_C	$T_f=25\text{ }^\circ\text{C}$, per 1 chip	60.6	W
Junction temperature	T_j	(Note 1)	-20 ~ +125	$^\circ\text{C}$

(Note1) The maximum junction temperature rating of the power chips integrated within the DIP-IPM is $150\text{ }^\circ\text{C} (@T_f \leq 100\text{ }^\circ\text{C})$ however, to insure safe operation of the DIP-IPM, the average junction temperature should be limited to $T_j(\text{ave}) \leq 125\text{ }^\circ\text{C} (@T_f \leq 100\text{ }^\circ\text{C})$.

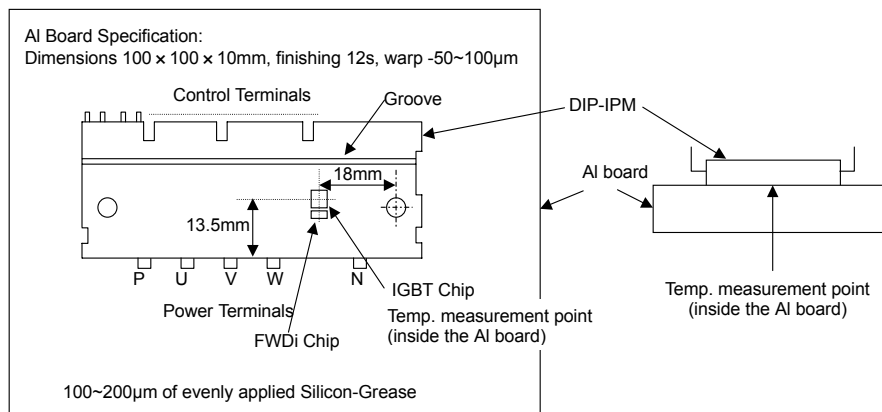
Control (Protection) Part :

Item	Symbol	Condition	Rating	Unit
Control supply voltage	V_D	Applied between $V_{P1}-V_{PC}, V_{N1}-V_{NC}$	20	V
Control supply voltage	V_{DB}	Applied between $V_{UFB}-V_{UFS}, V_{VFB}-V_{VFS}, V_{WFB}-V_{WFS}$	20	V
Input voltage	V_{IN}	Applied between $U_P, V_P, W_P-V_{PC}, U_N, V_N, W_N-V_{NC}$	-0.5 ~ $V_D+0.5$	V
Fault output supply voltage	V_{FO}	Applied between Fo- V_{NC}	-0.5 ~ $V_D+0.5$	V
Fault output current	I_{FO}	Sink current at Fo terminal	1	mA
Current sensing input voltage	V_{SC}	Applied between CIN- V_{NC}	-0.5 ~ $V_D+0.5$	V

Total System :

Item	Symbol	Condition	Rating	Unit
Self protection supply voltage limit (short circuit protection capability)	$V_{CC(prot)}$	$V_D=13.5\sim 16.5\text{V}$, Inverter part $T_j=125\text{ }^\circ\text{C}$, non-repetitive less than $2\mu\text{s}$	400	V
Module case operation temperature	T_f	(Note2)	-20 ~ +100	$^\circ\text{C}$
Storage temperature	T_{stg}		-40 ~ +125	$^\circ\text{C}$
Isolation voltage	Viso	60Hz, Sinusoidal, AC 1 minutes, connecting pins to heat-sink plate	2500	Vrms

(Note2) T_f measurement point :



Thermal Resistance :

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Junction to case thermal resistance (Note3)	$R_{th(j-f)Q}$	Inverter IGBT part (per 1/6 module)	-	-	1.65	°C / W
	$R_{th(j-f)F}$	Inverter FWD part (per 1/6 module)	-	-	3.00	

(Note3) Grease with good thermal conductivity should be applied evenly about +100 μ m ~ +200 μ m on the contact surface of DIP-IPM and a heat-sink.

Electrical Characteristics ($T_j=25^\circ\text{C}$, unless otherwise noted) :

Inverter Part :

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_D=V_{DB}=15\text{V}$ $V_{IN}=0\text{V}$	$I_C=30\text{A}$, $T_j=25^\circ\text{C}$	-	1.6	2.1	V
			$I_C=30\text{A}$, $T_j=125^\circ\text{C}$	-	1.7	2.2	
FWD forward voltage	V_{EC}	$T_j=25^\circ\text{C}$, $-I_C=30\text{A}$, $V_{IN}=5\text{V}$	-	1.5	2.0	V	
Switching times	t_{on}	$V_{CC}=300\text{V}$, $V_D=V_{DB}=15\text{V}$		0.7	1.3	1.9	μs
	t_{rr}	$I_C=30\text{A}$		-	0.3	-	
	$t_{c(on)}$	$T_j=125^\circ\text{C}$		-	0.4	0.6	
	t_{off}	Inductive load (upper-lower arm)		-	1.7	2.4	
	$t_{c(off)}$	$V_{IN}=5\text{V}$		-	0.5	0.8	
Collector-emitter cut-off current	I_{CES}	$V_{CE} = V_{CES}$	$T_j=25^\circ\text{C}$	-	-	1	mA
			$T_j=125^\circ\text{C}$	-	-	10	

Control (Protection) Part :

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	
Circuit current	I_D	$V_D=V_{DB}=15\text{V}$ $V_{IN}=5\text{V}$	Total of $V_{P1}-V_{PC}$, $V_{N1}-V_{NC}$	-	-	5.00	mA
			$V_{UFB}-V_{UFS}$, $V_{VFB}-V_{VFS}$, $V_{WFB}-V_{WFS}$	-	-	0.40	mA
		$V_D=V_{DB}=15\text{V}$ $V_{IN}=0\text{V}$	Total of $V_{P1}-V_{PC}$, $V_{N1}-V_{NC}$	-	-	7.00	mA
			$V_{UFB}-V_{UFS}$, $V_{VFB}-V_{VFS}$, $V_{WFB}-V_{WFS}$	-	-	0.55	mA
Fo output voltage	V_{FOH}	$V_{SC}=0\text{V}$, Fo circuit pull-up to 5V with 10k Ω	4.9	-	-	V	
	V_{FOL}	$V_{SC}=1\text{V}$, $I_{FO}=1\text{mA}$	-	-	0.95	V	
Input current	I_{IN}	$V_{IN}=5\text{V}$	1.0	1.50	2.0	mA	
short circuit trip level	$V_{SC(ref)}$	$T_j=25^\circ\text{C}$, $V_D=15\text{V}$ (Note4)	0.43	0.48	0.53	V	
Supply circuit under-voltage protection	UV_{DBt}	$T_j \leq 125^\circ\text{C}$	Trip level	10.0	-	12.0	V
	UV_{DBr}		Reset level	10.5	-	12.5	V
	UV_{Dt}		Trip level	10.3	-	12.5	V
	UV_{Dr}		Reset level	10.8	-	13.0	V
Fault output pulse width	t_{FO}	$C_{FO}=22\text{nF}$ (Note5)	1.0	1.8	-	ms	
ON threshold voltage	$V_{th(on)}$	Applied between U_P, V_P, W_P-V_{PC} ,	2.1	2.3	2.6	V	
OFF threshold voltage	$V_{th(off)}$	U_N, V_N, W_N-V_{NC}	0.8	1.4	2.1		

(Note4) Short circuit protection is functioning only at the low-arms. Please select the value of the external shunt resistor such that the SC trip-level is less than 51A

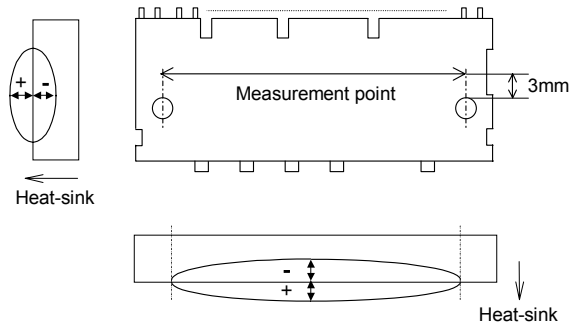
(Note5) Fault signal is output when the low-arms short circuit or control supply under-voltage protective functions operate. The fault output pulse-width t_{FO} depends on the capacitance value of C_{FO} according to the following approximate equation : $C_{FO} = 12.2 \times 10^{-6} \times t_{FO}$ [F]

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Mechanical Characteristics and Ratings :

Item	Condition		Min.	Typ.	Max.	Unit
Mounting torque	Mounting screw: M4	Recommended: 1.18 N·m	0.98	–	1.47	N·m
Weight			–	65	–	g
Heat-sink flatness	(Note6)		–50	–	100	μm

(Note6)



Recommended Operation Conditions :

Item	Symbol	Condition	Recommended			Unit	
			Min.	Typ.	Max.		
Supply voltage	V_{CC}	Applied between P-N	0	300	400	V	
Control supply voltage	V_D	Applied between V_{P1} - V_{PC} , V_{N1} - V_{NC}	13.5	15.0	16.5	V	
Control supply voltage	V_{DB}	Applied between V_{UFB} - V_{UFS} , V_{VFB} - V_{VFS} , V_{WFB} - V_{WFS}	13.0	15.0	18.5	V	
Control supply variation	$\Delta V_D, \Delta V_{DB}$		-1	-	1	V/μs	
Arm-shoot-through blocking time	t_{dead}	For each input signal, $T_f \leq 100^\circ\text{C}$	2	-	-	μs	
PWM input frequency	f_{PWM}	$T_f \leq 100^\circ\text{C}$, $T_j \leq 125^\circ\text{C}$	-	-	20	kHz	
Allowable r.m.s current	I_o	$V_{CC}=300\text{V}$, $V_D=V_{DB}=15\text{V}$, P.F=0.8, sinusoidal PWM, $T_j \leq 125^\circ\text{C}$, $T_f \leq 100^\circ\text{C}$ (Note7)	$f_{PWM}=5\text{kHz}$	-	-	19	Arms
			$f_{PWM}=15\text{kHz}$	-	-	11.6	
Minimum input pulse width	PWIN(on)		(Note8)	0.3	-	-	μs
	PWIN(off)	200 V_{CC} 350V, 13.5 V_D 16.5V, 13.0 V_{DB} 18.5V, -20 T_f 100 , N-line wiring inductance less than 10nH (Note 9)	Below rated current	1.5	-	-	
			Between rated current and 1.7 times of rated current	3.0	-	-	
V_{NC} variation	V_{NC}	between V_{NC} -N (including surge)	-5.0	-	5.0	V	

(Note 7) The Allowable r.m.s. current value depends on the actual application conditions.

(Note 8) Input signal with ON pulse width less than PWIN(on) might make no response.

(Note 9) IPM might not work properly or make response for the Input signal with OFF pulse width less than PWIN(off). Please refer to Fig. 5 for recommended wiring method.

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Fig.2 The DIP-IPM Internal Circuit :

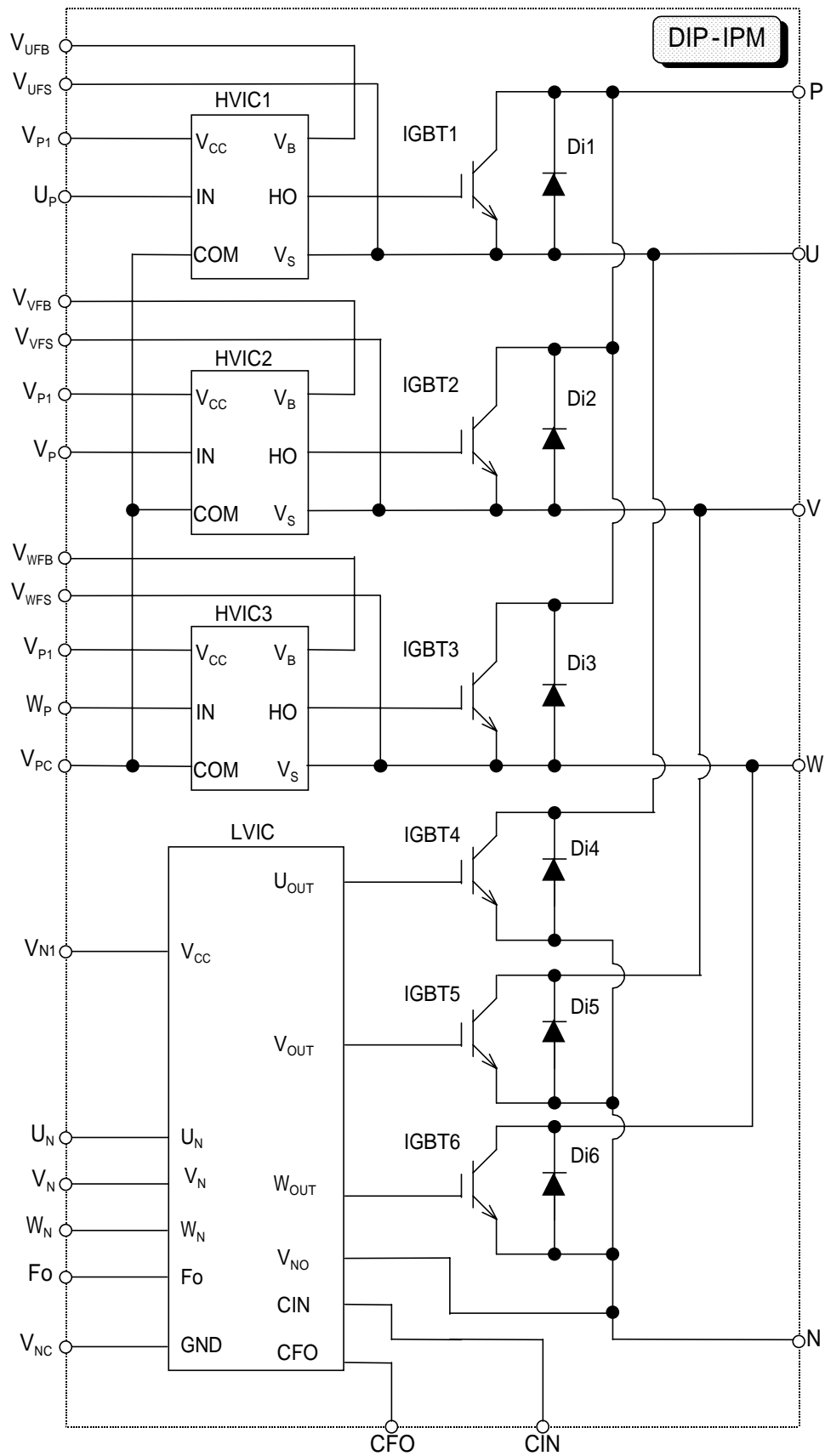
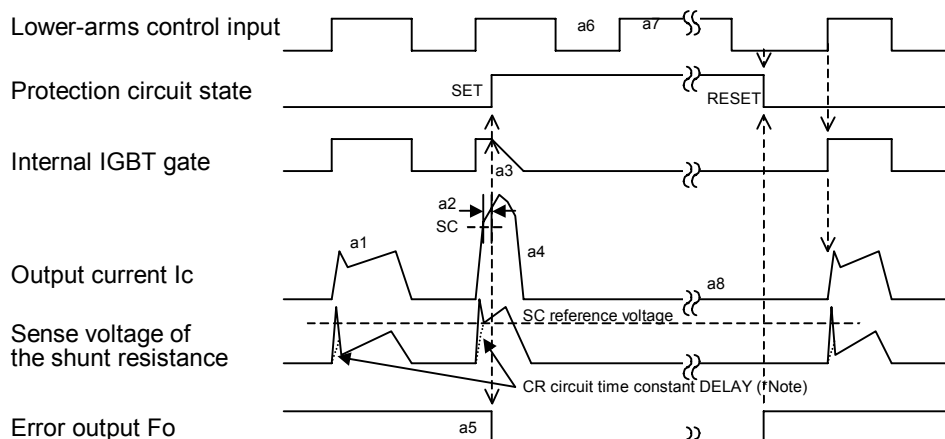


Fig.3 Timing Charts of the DIP-IPM Protective Functions**[A] Short-Circuit Protection (Lower-arms only)**

(For the external shunt resistance and CR connection)

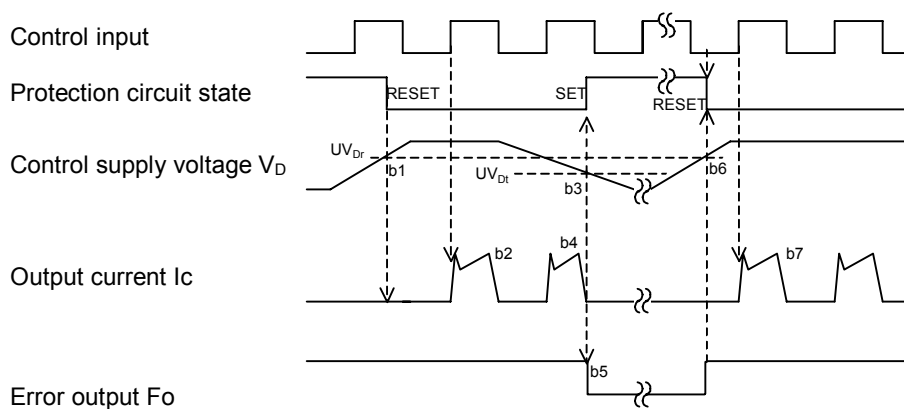
- a1. Normal operation : IGBT ON and carrying current.
- a2. Short circuit current detection (SC trigger).
- a3. Hard IGBT gate interrupt.
- a4. IGBT turns OFF.
- a5. Fo timer operation starts : The pulse width of the Fo signal is set by the external capacitor C_{FO} .
- a6. Input "L" : IGBT OFF state.
- a7. Input "H" : IGBT ON state, but during the Fo active signal the IGBT doesn't turn ON.
- a8. IGBT OFF state.



(*note) The CR time constant safe guards against erroneous SC signal resulting from di/dt generated voltages when the IGBT turns ON. The optimum setting for the CR circuit time constant is 1.5~2.0 μ s.

[B] Under- Voltage Protection (Lower-arm, UV_D)

- b1. Control supply voltage rises : After the voltage level reaches UV_{Dr} , the circuits start to operate when the next input is applied.
- b2. Normal operation : IGBT ON and carrying current.
- b3. Under voltage trip (UV_{Dt}).
- b4. IGBT OFF in spite of control input condition.
- b5. Fo operation starts.
- b6. Under voltage reset (UV_{Dr}).
- b7. Normal operation : IGBT ON and carrying current.



[C] Under- Voltage Protection (Upper-arm, UV_{DB})

- c1. Control supply voltage rises : After the voltage level reaches UV_{DBr} , the circuits start to operate when the next input is applied.
- c2. Normal operation : IGBT ON and carrying current.
- c3. Under voltage trip (UV_{DBt}).
- c4. IGBT OFF in spite of control input condition, but there is no Fo signal output.
- c5. Under voltage reset (UV_{DBr}).
- c6. Normal operation : IGBT ON and carrying current.

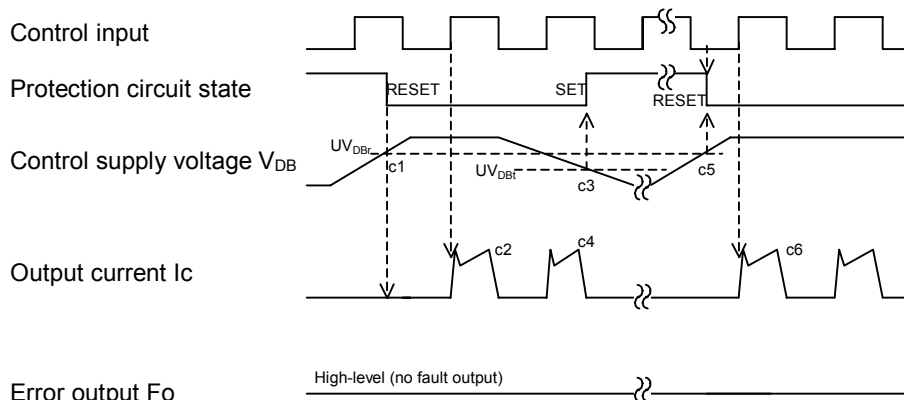
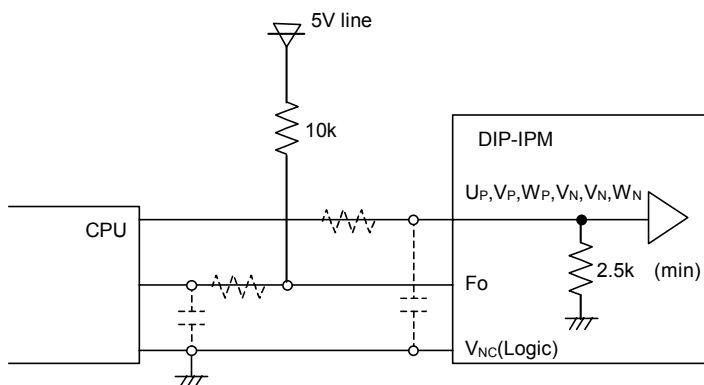


Fig.4 Recommended CPU I/O interface circuit :



Note) RC coupling at each input (parts shown dotted) may change depending on the PWM control scheme used in the application and on the wiring impedance of the application's printed circuit board. The DIP-IPM input signal section integrates a 2.5k (min) pull-down resistor. Therefore, when an external filtering resistor is used, care must be taken to satisfy the turn-on threshold voltage requirement.

Fig.5 Recommended wiring of shunt resistor :

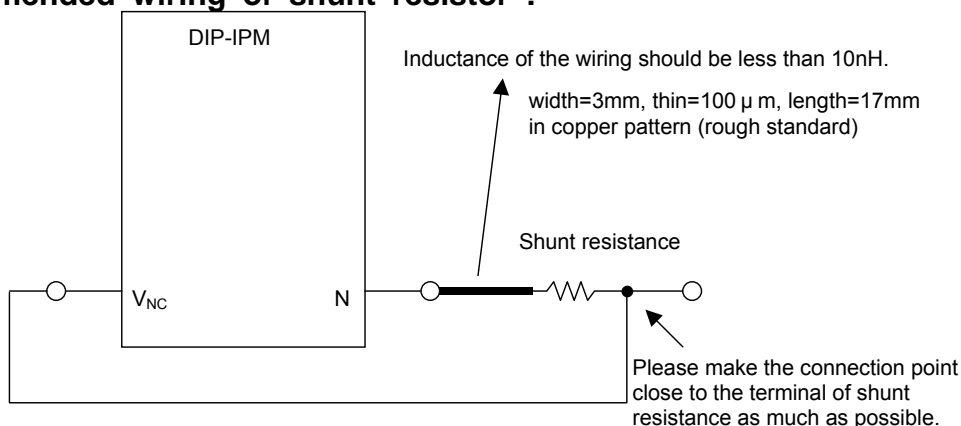
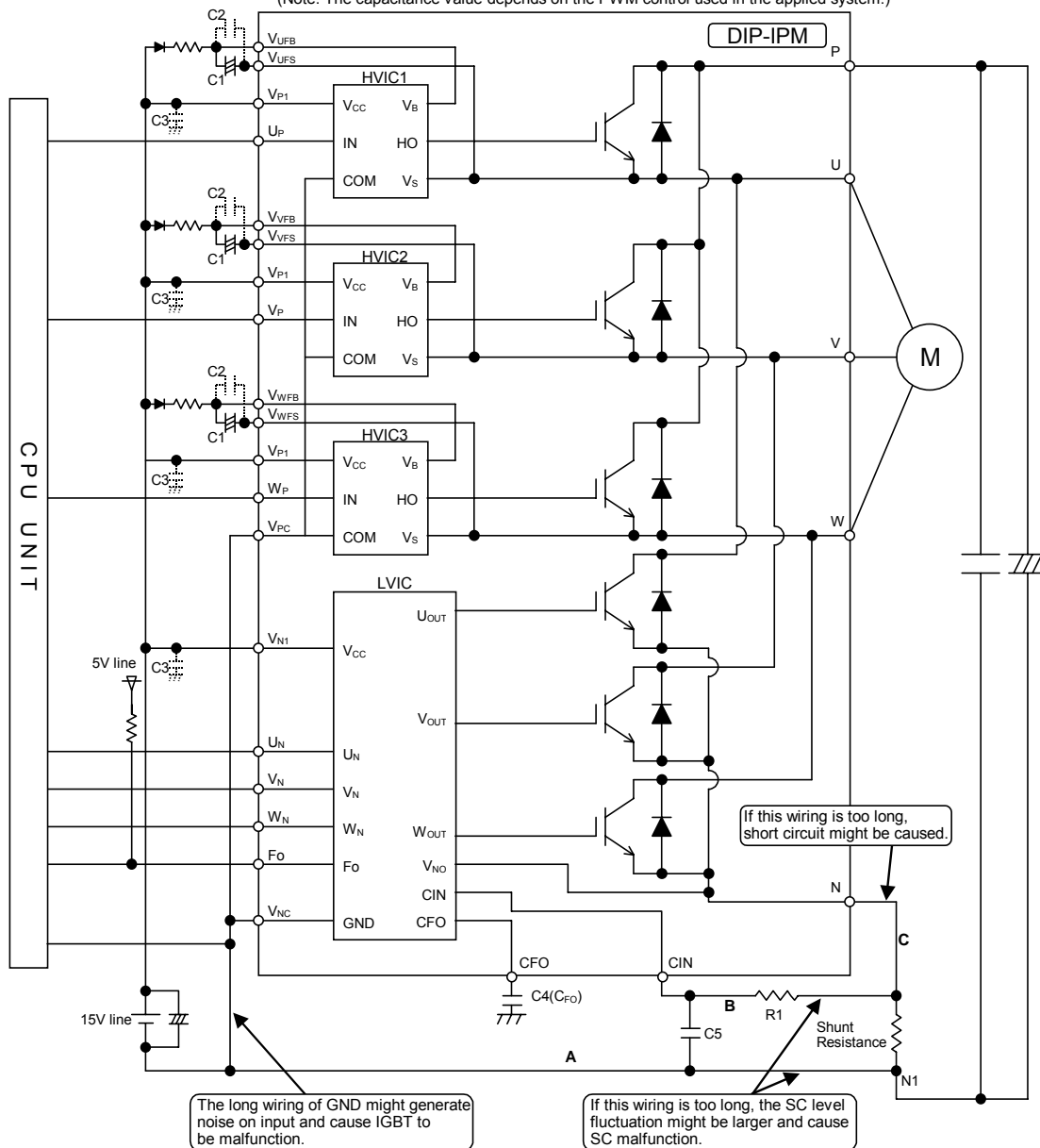


Fig.6 Typical DIP-IPM Application Circuit Example :

C1:Tight tolerance temp-compensated electrolytic type
C2,C3: 0.1~0.22 μ F R-category ceramic capacitor for noise filtering.
(Note: The capacitance value depends on the PWM control used in the applied system.)



- Note1) To prevent the input signals oscillation, the wiring of each input should be as short as possible. (Less than 2cm)
- Note2) By virtue of integrating an application specific type HVIC inside the module, direct coupling to CPU terminals without any opto-coupler or transformer isolation is possible.
- Note3) Fo output is open collector type. This signal line should be pulled up to the positive side of the 5V power supply with approximately 10k Ω resistance.
- Note4) Fo output pulse width should be decided by connecting an external capacitor between CFO and V_{NC} terminals (C_{FO}). (Example: C_{FO} = 22 nF \rightarrow t_{FO} = 1.8 ms (typ.))
- Note5) The logic of input signal is active high. The DIP-IPM input signal section integrates a 2.5k (min) pull-down resistor. Therefore, when an external filtering resistor is used, care must be taken to satisfy the turn-on threshold voltage requirement.
- Note6) To prevent errors of the protection function, the wiring of A, B, C should be as short as possible.
- Note7) In the recommended protection circuit, please select the R1C5 time constant in the range 1.5~2 μ s.
- Note8) Each capacitor should be put as nearby the pins of the DIP-IPM as possible.
- Note9) To prevent surge destruction, the wiring between the smoothing capacitor and the P&N1 pins should be as short as possible. Approximately a 0.1~0.22 μ F snubber capacitor between the P&N1 pins is recommended.

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